

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P55K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

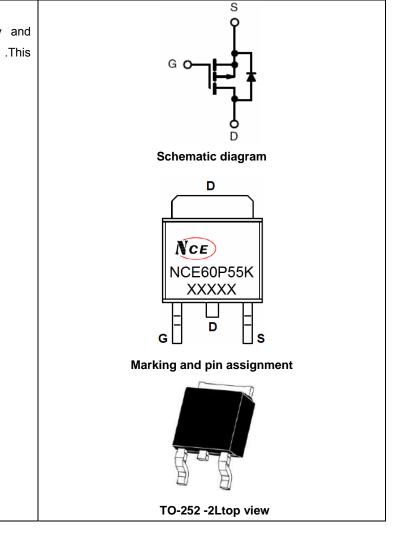
- V_{DS} =-60V,I_D =-55A
 R_{DS(ON)} <28mΩ @ V_{GS}=-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- High side switch for full bridge converter
- DC/DC converter for LCD display

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P55K	NCE60P55K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	-55	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	-24.8	А
Pulsed Drain Current	I _{DM}	-220	А
Maximum Power Dissipation	PD	110	W
Derating factor		0.73	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	273	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C



Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.36	°C/W]
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Electrical Characteristics (T_c=25[°]C unless otherwise noted)

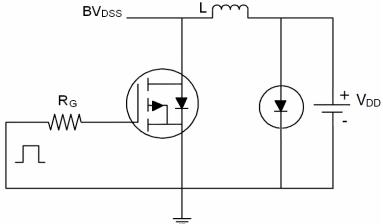
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	····					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-2	-2.6	-3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	23	28	mΩ
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)			·			•
Input Capacitance	C _{lss}	V _{DS} =-30V,V _{GS} =0V, F=1.0MHz	-	3016.8	-	PF
Output Capacitance	Coss		-	180	-	PF
Reverse Transfer Capacitance	C _{rss}		-	126	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	tr	V_{DD} =-30V, R _L =1.5 Ω ,	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V,R _G =3Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg		-	49.8		nC
Gate-Source Charge	Q _{gs}	V _{DS} =-30,I _D =-20A, V _{GS} =-10V	-	10.6		nC
Gate-Drain Charge	Q _{gd}	V _{GS} 10V	-	13.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-55	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =- 20A	-	47		nS
Reverse Recovery Charge	Qrr	di/dt = -100A/µs ^(Note3)	-	53		nC

Notes:

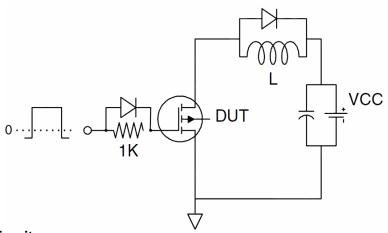
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^\circ\!\mathrm{C}$,V_{DD}=-20V,V_G=-10V,L=0.5mH,Rg=25\Omega



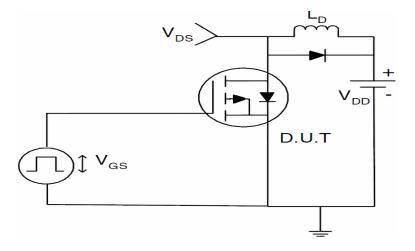
Test Circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

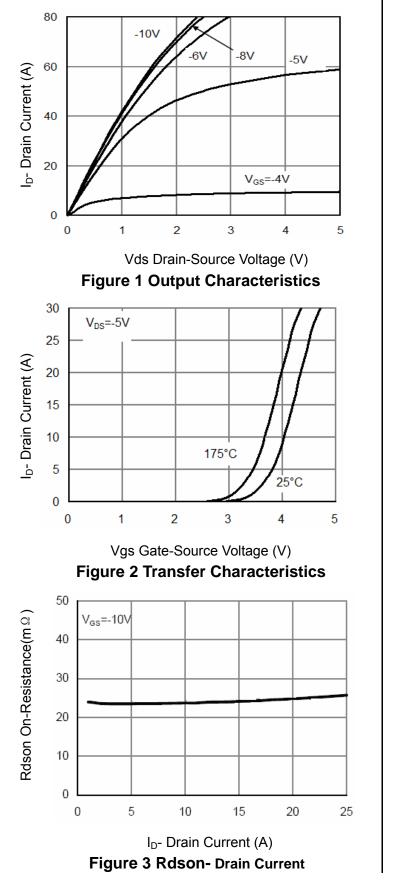


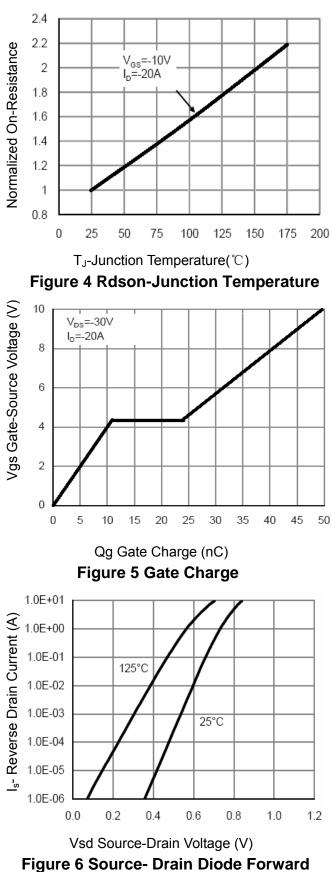
3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

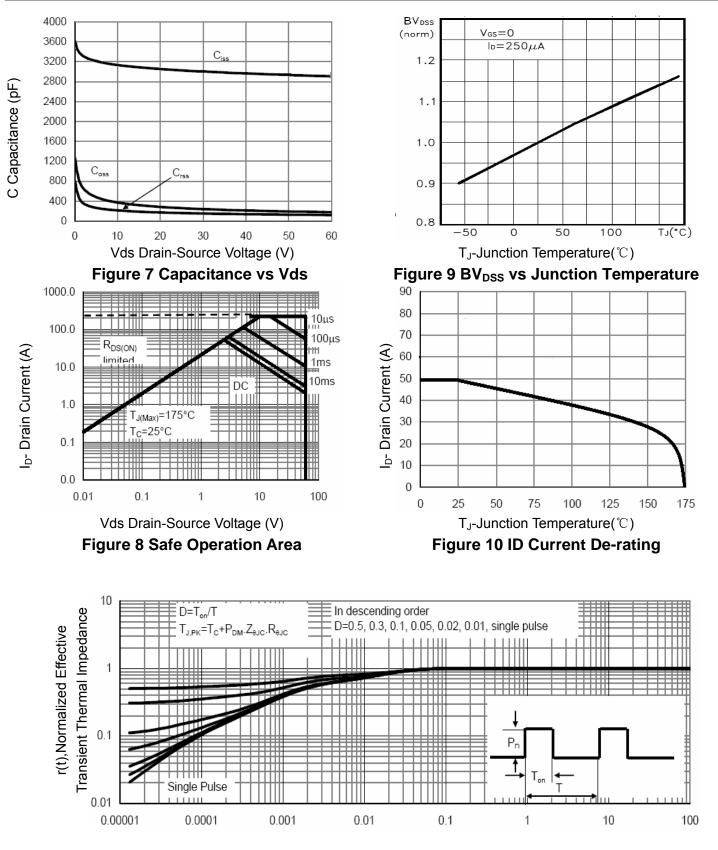






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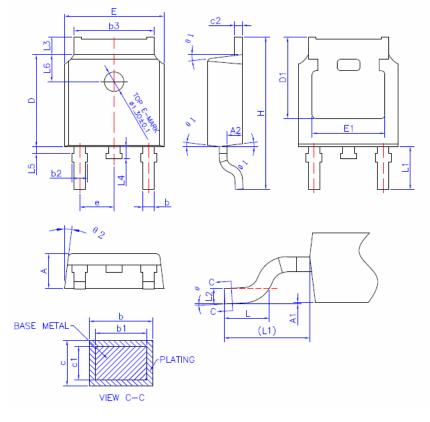
NCE60P55K



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX		
А	2.20	2.30	2.38		
A1	0	—	0,10		
A2	0,90	1,01	1,10		
b	0.72	—	0.85		
b1	0.71	0.76	0.81		
b2	0,72	—	0,90		
b3	5,13	5,33	5,46		
с	0.47	—	0.60		
c1	0.46	0.51	0.56		
c2	0,47	—	0,60		
D	6.00	6,10	6,20		
D1	5.25	—			
E	6.50	6.60	6.70		
E1	4,70	—			
е	2,186	2,286	2,386		
Н	9.80	10.10	10.40		
L	1.40	1.50	1.70		
L1	2	2,90 REF			
L2	0.508 BSC				
L3	0.90	—	1.25		
L4	0.60	0.80	1.00		
L5	0,15	—	0,75		
L6	1.80 REF				
θ	0°	—	8°		
θ1	5°	7°	9°		
θ2	5°	7°	9°		



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